

RJK1054DPB

100V, 20A, $22m\Omega$ max. Silicon N Channel Power MOS FET Power Switching

R07DS0093EJ0300 Rev.3.00 Apr 11, 2013

Features

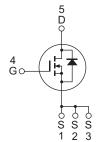
- High speed switching
- Low drive current
- Low on-resistance $R_{DS(on)} = 17 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V})$

- Pb-free
- Halogen-free
- High density mounting

Outline

RENESAS Package code: PTZZ0005DA-A (Package name: LFPAK)





1, 2, 3 Source 4 Gate

Gate Drain

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	100	V	
Gate to source voltage	V_{GSS}	±20	V	
Drain current	I _D	20	А	
Drain peak current	I _{D(pulse)} Note1	80	А	
Body-drain diode reverse drain current	I _{DR}	20	А	
Avalanche current	I _{AP} Note 2	20	А	
Avalanche energy	E _{AS} Note 2	4.0	mJ	
Channel dissipation	Pch Note3	55	W	
Channel to Case Thermal Resistance	θch-C	2.27	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at L=10uH, Tch = 25°C, Rg \geq 50 Ω
- 3. Tc = 25°C

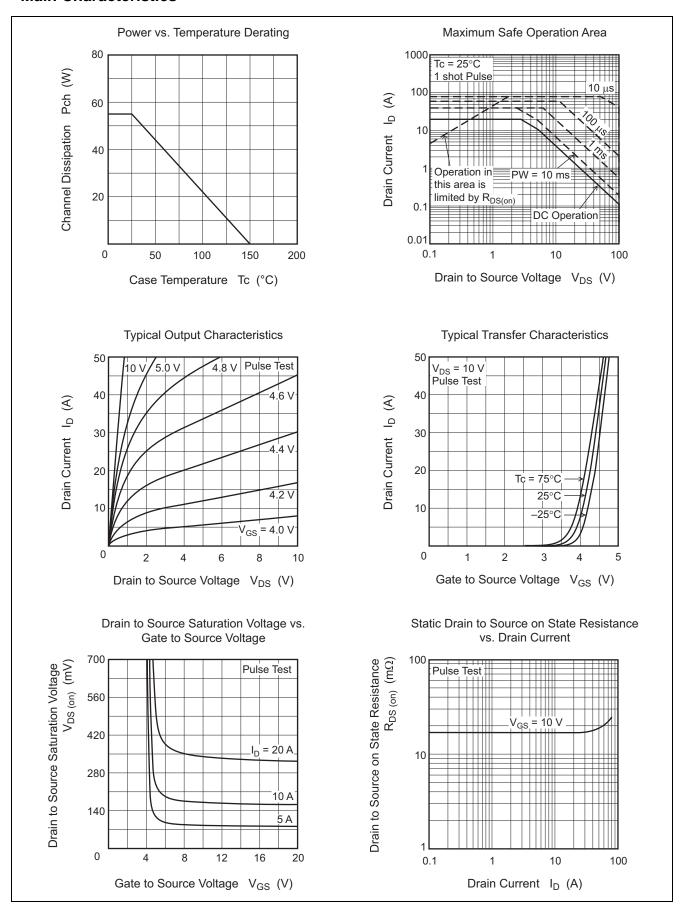
Electrical Characteristics

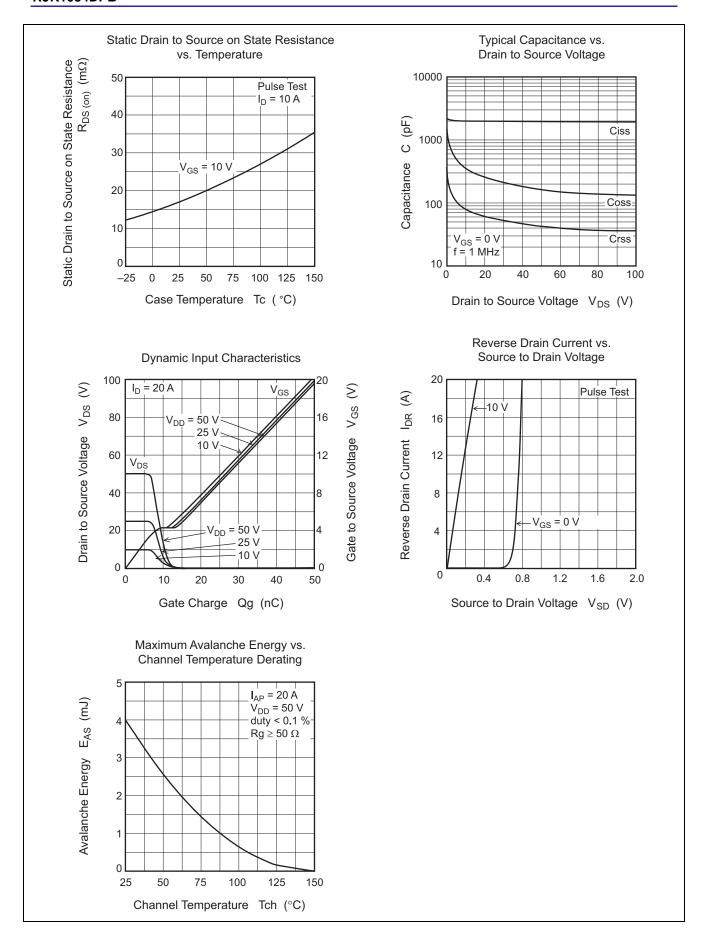
 $(Ta = 25^{\circ}C)$

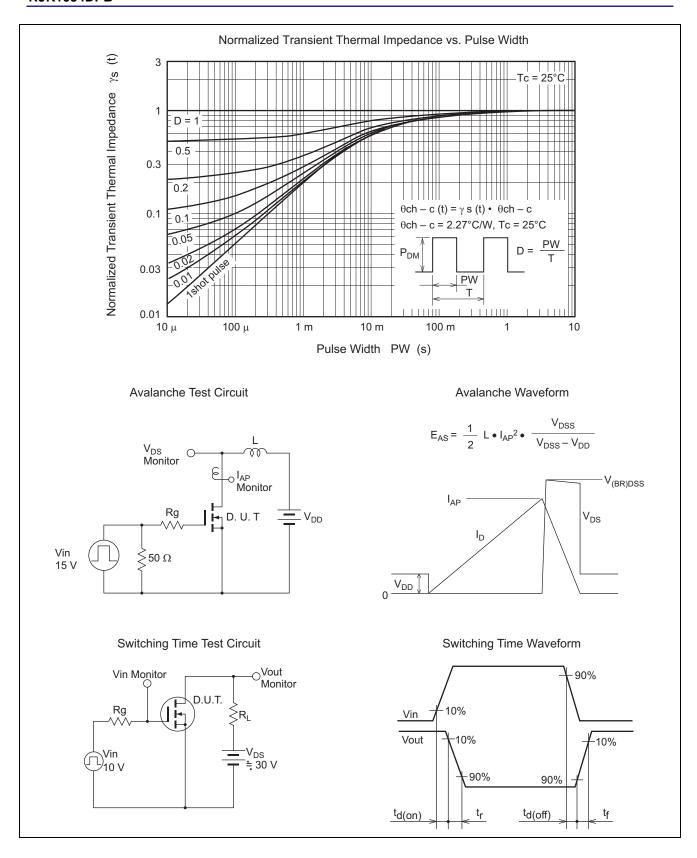
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source cutoff voltage	V _{GS(off)}	2.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	17	22	mΩ	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}	_	32	_	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2000	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	350	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	80	_	pF	
Gate Resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	27	_	nC	$V_{DD} = 50 \text{ V}, V_{GS} = 10 \text{ V},$
Gate to source charge	Qgs	_	9.0	_	nC	I _D = 20 A
Gate to drain charge	Qgd	_	4.5	_	nC	
Turn-on delay time	t _{d(on)}	_	12	_	ns	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A},$
Rise time	t _r	_	3.8	_	ns	$V_{DD} \cong 30 \text{ V}, R_L = 3 \Omega,$
Turn-off delay time	t _{d(off)}	_	32	_	ns	$Rg = 4.7 \Omega$
Fall time	t _f	_	5.4	_	ns	
Body-drain diode forward voltage	V_{DF}	_	0.8	1.1	V	$I_F = 20 \text{ A}, V_{GS} = 0 \text{ V}^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	48	_	ns	I _F = 20 A, V _{GS} = 0 V
						di _F / dt = 100 A/ μs

Notes: 4. Pulse test

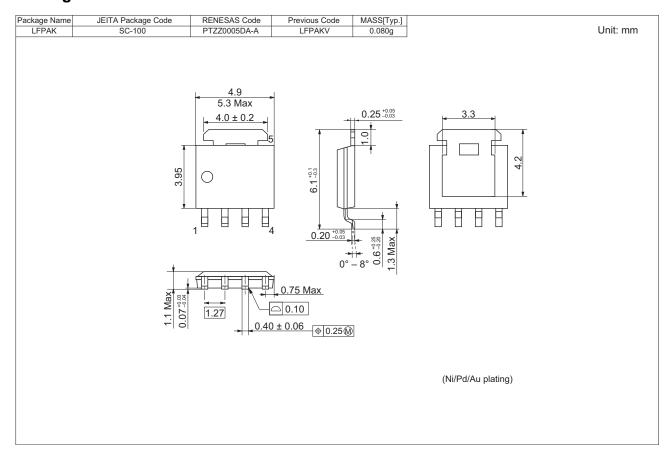
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1054DPB-00-J5	2500 pcs	Taping

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Renesas Electronics America Inc. 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A. Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited 1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Milliboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd. 7th Floor, Quantum Plaza, No.27 ZhiChunLu Ha Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 i. nunLu Haidian District. Beiiing 100083. P.R.China

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2868-9318, Fax: +852 2869-9022/9044

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949 Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd. 11F., Samik Lavied' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea Tel: 482-2558-3737, Fax: 482-2558-5141

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